

first wells formed in said first regions, respectively; and

a second well formed in a second region deeper than each of said first wells in said semiconductor substrate, said second well being in contact with some of said first wells to provide electrical connection therebetween and not being in contact with said first wells adjacent to said some of said first wells,

wherein said first and second wells of said first and second regions on one side with reference to a predetermined boundary are of a first conductivity type, and said first wells on the other side are of a second conductivity type.

14. (Amended) A semiconductor device according to claim 13, wherein said first and second wells of said first and second regions on one side with reference to the predetermined boundary are of a first conductivity type, and said first wells on the other side are of a second conductivity type.

15. (Amended) A semiconductor device comprising:

a semiconductor substrate;

an element isolation film formed such as to have a predetermined depth from a main surface of said semiconductor substrate, said element isolation film dividing the area from said main surface to said depth into a plurality of first regions;

first wells formed in said first regions, respectively; and

a second well formed in a second region deeper than said first wells in said semiconductor substrate, said second well having a higher concentration than said first wells and being in contact with a plurality of said first wells,

wherein said first and second wells of said first and second regions on one side with reference to a predetermined boundary are of a first conductivity type, and said first and second wells on the other side are of a second conductivity type.

16. (Amended) A semiconductor device comprising:
a semiconductor substrate;
a plurality of element isolation films formed such as to have a predetermined uniform depth from a main surface of said semiconductor substrate, said element isolation films dividing the area from said main surface to said depth into a plurality of first regions;
first wells formed in said first regions, respectively; and
a second well formed in a second region deeper than each of said first wells in said semiconductor substrate, said second well being in contact with some of said first wells,
wherein said first and second wells of said first and second regions on one side with reference to a predetermined boundary are of a first conductivity type, and said first wells on the other side are of a second conductivity type.

20. (Amended) A semiconductor device according to claim 1, wherein each of the first wells comprises a single element.

21. (Amended) A semiconductor device according to claim 13, wherein each of the first wells comprises a single element.

22. (Amended) A semiconductor device according to claim 15, wherein each of the first wells comprises a single element.

23. (Amended) A semiconductor device according to claim 16, wherein each of the first wells comprises a single element.

Please add new Claim 24 as follows:

24. (New) A semiconductor device according to claim 15, wherein the second well is in contact with all of the first wells.